

PSMN8R5-60YS

N-channel LFPAK 60 V, 8 mΩ standard level MOSFET

22 July 2015

Product data sheet

1. General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

3. Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Motor control
- Server power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>		-	-	76	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	106	W
Tj	junction temperature			-55	-	175	°C
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 °C;$ Fig. 12		-	-	12.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13		-	5.6	8	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 60 A; V _{DS} = 30 V; Fig. 15; Fig. 14		-	7.7	-	nC



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{G(tot)}	total gate charge	$V_{GS} = 10 \text{ V}; I_D = 60 \text{ A}; V_{DS} = 30 \text{ V};$ Fig. 14; Fig. 15	-	39	-	nC
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 76 A; $V_{sup} \le$ 60 V; R_{GS} = 50 Ω ; unclamped	-	-	97	mJ

Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	S	source	mb	D		
2	S	source	ļ ļ			
3	S	source	q		[q]	G T A
4	G	gate	فققف	mbb076 S		
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)			

Ordering information

Table 3. **Ordering information**

Type number	Package				
	Name	Description	Version		
PSMN8R5-60YS	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

Marking

Table 4. Marking codes

Type number	Marking code
PSMN8R5-60YS	8R560

Limiting values 8.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	60	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}; R_{GS} = 20 \text{k}\Omega$	-	60	V

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Symbol	Parameter	Conditions	Min	Max	Unit
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	106	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	54	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	76	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3	-	303	Α
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-drai	n diode		<u> </u>		
I _S	source current	T _{mb} = 25 °C	-	76	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	303	Α
Avalanche r	ruggedness		'		,
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 76 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; unclamped	-	97	mJ

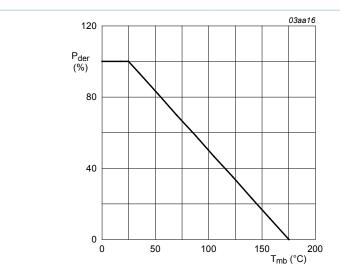


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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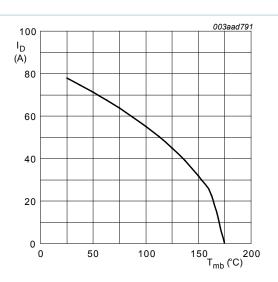


Fig. 2. Continuous drain current as a function of mounting base temperature



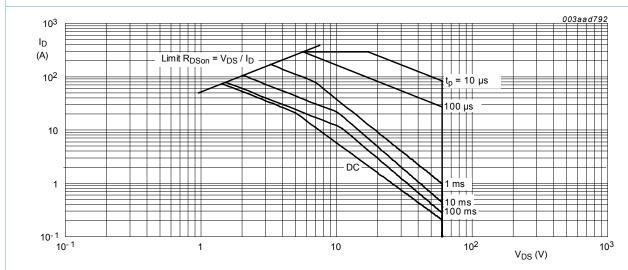


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.63	1.42	K/W

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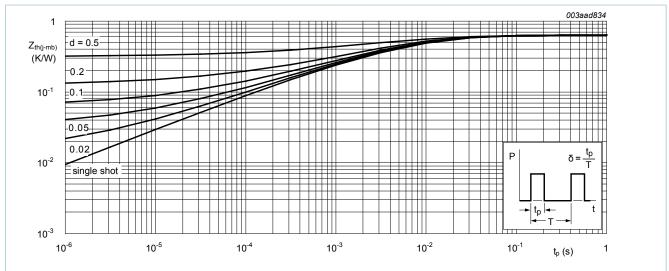


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	2	3	3.8	V
V_{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 11	-	-	4.3	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 11	0.95	-	-	V	
I _{DSS} drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.03	2	μA	
	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 125 °C	-	-	50	μA	
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 15 A; T_{j} = 175 °C; Fig. 12	-	12	18.4	mΩ
	V_{GS} = 10 V; I_D = 15 A; T_j = 100 °C; Fig. 12	-	-	12.8	mΩ	
		V_{GS} = 10 V; I_{D} = 15 A; T_{j} = 25 °C; Fig. 13	-	5.6	8	mΩ
R_G	gate resistance	f = 1 MHz	-	0.61	-	Ω

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 14; Fig. 15	-	39	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	33	-	nC
Q_{GS}	gate-source charge	I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 15; Fig. 14	-	13.3	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	I_D = 60 A; V_{DS} = 30 V; V_{GS} = 10 V; Fig. 14	-	7	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	6.2	-	nC
Q_{GD}	gate-drain charge	I _D = 60 A; V _{DS} = 30 V; V _{GS} = 10 V; Fig. 15; Fig. 14	-	7.7	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 30 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	5.2	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16$	-	2370	-	pF
C _{oss}	output capacitance		-	307	-	pF
C _{rss}	reverse transfer capacitance		-	172	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 0.5 Ω ; V_{GS} = 10 V;	-	18.4	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	13.7	-	ns
t _{d(off)}	turn-off delay time		-	32.4	-	ns
t _f	fall time		-	9.2	-	ns
Source-drai	in diode					
V_{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	43.3	-	ns
Q _r	recovered charge	V _{DS} = 30 V	-	61.4	-	nC

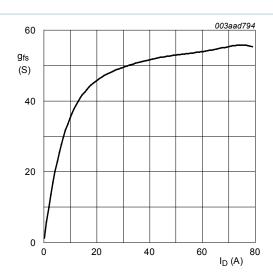


Fig. 5. Forward transconductance as a function of drain current; typical values

$$T_j = 25$$
 °C; $V_{DS} = 20$ V

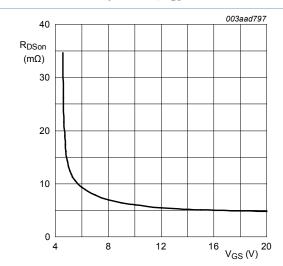


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
 °C; $I_D = 20$ A

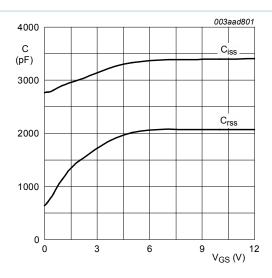


Fig. 6. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

$$V_{DS} = 0 \text{ V; } f = 1 \text{ MHz}$$

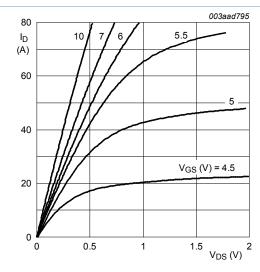


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25 \,^{\circ}C$$

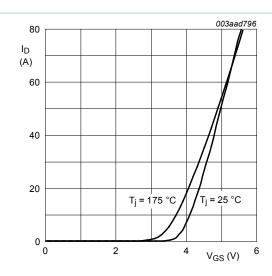


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



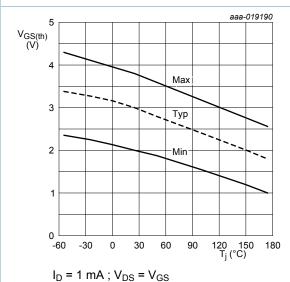
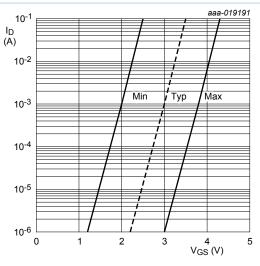


Fig. 11. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \, ^{\circ}C; \, V_{DS} = 5V$

Fig. 10. Sub-threshold drain current as a function of gate-source voltage

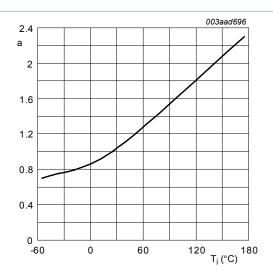


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

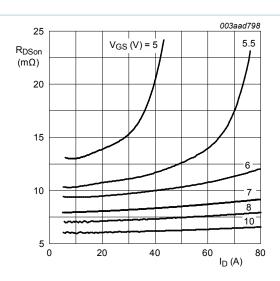


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

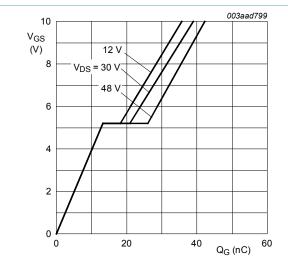


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
 °C; $I_D = 60$ A

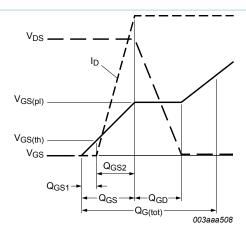


Fig. 14. Gate charge waveform definitions

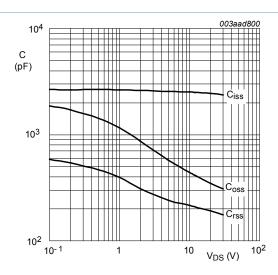


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

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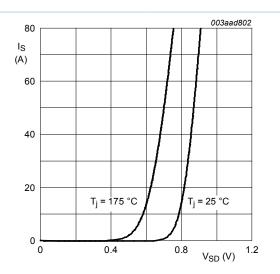
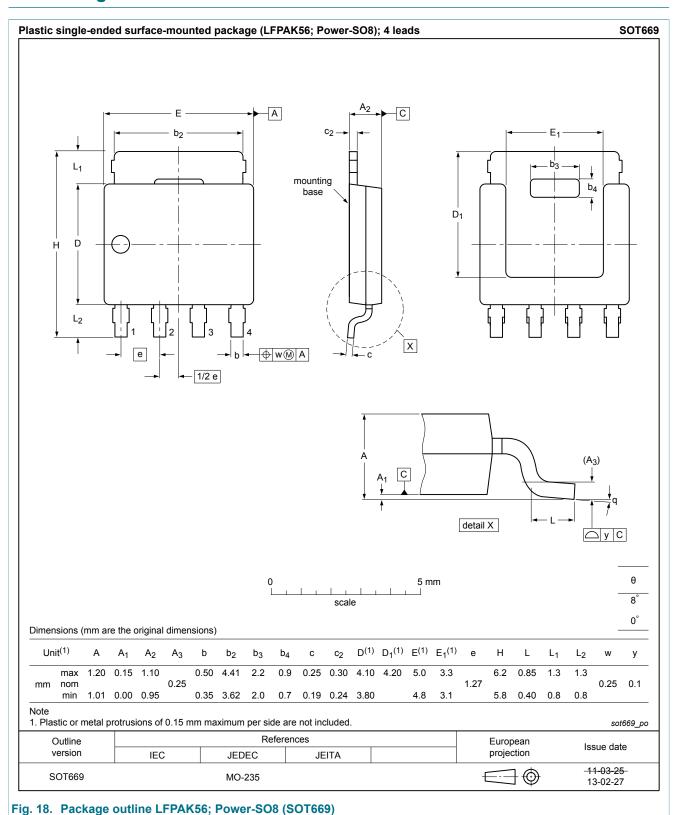


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline



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